





Package: SuperSOT-6 single Mark : .S1

# **PNP Low Saturation Transistor**

This device is designed with high current gain and low saturation voltage with collector currents up to 2A continous. Sourced from process PB.

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	35	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current- Continuous - Peak Pulse Current	1 2	A A
TJ, TSTG	Operating and Storage Junction Temperature Range	-55 to +150	°C

These ratings are limiting values above which the serviceability of any semiconductor device may be impaired. <u>NOTES:</u>

1) These ratings are based on a maximum junction temperature of 150°C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristics	Мах	Units
PD	Total Device Dissipation*	700	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, total	180	°C/W
	*Device mounted on a 1 in2 pad of 2 oz copper.		

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	Electrical Characteristics T <sub>A</sub> = 25°C unless otherwise noted							
Parameter	Test Conditions	Min	Мах	Units				
RACTERISTICS								
Collector to Emitter Voltage	Ic = 10 mA	30		V				
Collector to Base Voltage	Ic = 100 uA	35		V				
Emitter to Base Voltage	le = 100 uA	5		V				
Collector Cutoff Current	Vcb = 30 V Vcb = 30 V, Ta= 100C		100 10	nA uA				
Emitter Cutoff Current	Veb = 4 V		100	nA				
	1							
DC Current Gain	$\begin{array}{llllllllllllllllllllllllllllllllllll$	70 100 80 40 100	300	-				
Collector-Emitter Saturation Voltage	$      Ic = 250 \text{ mA},  Ib = 25 \text{ mA} \\       Ic = 500 \text{ mA},  Ib = 50 \text{ mA} \\       Ic = 1 \text{ A},  Ib = 100 \text{ mA} \\       Ic = 2 \text{ A},  Ib = 200 \text{ mA} $		200 350 500 750	mV mV mV mV				
Base-Emitter Saturation Voltage	Ic = 1 A, Ib = 100 mA		1.25	V				
Base-Emitter On Voltage	Ic = 1 A, Vce = 2 V		1	V				
Output Capacitance	Vcb = 10V, f = 1MHz		25	pF				
Current Gain - Bandwidth Product	Vce = 5 V, Ic = 100mA, f = 100MHz	100		MHz				
	Collector to Emitter Voltage Collector to Base Voltage Emitter to Base Voltage Collector Cutoff Current Emitter Cutoff Current ACTERISTICS DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage GNAL CHARACTERISTICS Output Capacitance	Collector to Emitter VoltageIc = 10 mACollector to Base VoltageIc = 100 uAEmitter to Base VoltageIe = 100 uACollector Cutoff CurrentVcb = 30 V Vcb = 30 V, Ta= 100CEmitter Cutoff CurrentVeb = 4 VACTERISTICSDC Current GainDC Current GainVce = 2V, Ic = 50 mA Vce = 2V, Ic = 500 mA Vce = 2V, Ic = 1 A Vce = 2X, Ic = 500 mACollector-Emitter Saturation VoltageIc = 250 mA, Ib = 25 mA Ic = 500 mA Ic = 1 A, Ib = 100 mA Ic = 2 A, Ib = 200 mABase-Emitter Saturation VoltageIc = 1 A, Ib = 100 mA Ic = 2 A, Ib = 200 mABase-Emitter On VoltageIc = 1 A, Vce = 2 VGNAL CHARACTERISTICSVcb = 10V, f = 1MHz	Collector to Emitter VoltageIc = 10 mA30Collector to Base VoltageIc = 100 uA35Emitter to Base VoltageIe = 100 uA5Collector Cutoff CurrentVcb = 30 V Vcb = 30 V, Ta= 100C5Emitter Cutoff CurrentVeb = 4 V70Emitter Cutoff CurrentVeb = 4 V70ACTERISTICSVce = 2V, Ic = 50 mA Vce = 2V, Ic = 500 mA Vce = 2V, Ic = 500 mA Vce = 2V, Ic = 1 A Vce = 2V, Ic = 2 A 40 Vce = 0.8V, Ic = 500 mA 10070Collector-Emitter Saturation VoltageIc = 250 mA, Ib = 25 mA Ic = 1 A, Ib = 100 mA Ic = 2 A, Ib = 200 mA70Base-Emitter Saturation VoltageIc = 1 A, Ib = 100 mA Ic = 1 A, Vce = 2 V100Base-Emitter On VoltageIc = 1 A, Vce = 2 V100COLLECTORVcb = 10V, f = 1MHz100	Collector to Emitter VoltageIc = 10 mA30Collector to Base VoltageIc = 100 uA35Emitter to Base VoltageIe = 100 uA5Collector Cutoff CurrentVcb = 30 V Vcb = 30 V, Ta= 100C100 10Emitter Cutoff CurrentVeb = 4 V100Emitter Cutoff CurrentVce = 2V, Ic = 50 mA Vce = 2V, Ic = 500 mA70 100ACTERISTICSVce = 2V, Ic = 50 mA Vce = 2V, Ic = 500 mA 100300Collector-Emitter Saturation VoltageIc = 250 mA, Ib = 25 mA Ic = 500 mA Vce = 2A, Ib = 100 mA200 350 1c = 1 A, Ib = 100 mACollector-Emitter Saturation VoltageIc = 1 A, Ib = 100 mA1.25Base-Emitter On VoltageIc = 1 A, Vce = 2 V1GNAL CHARACTERISTICSVcb = 10V, f = 1MHz25				

FMBS549



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